

SOT-89 Plastic-Encapsulate Transistors

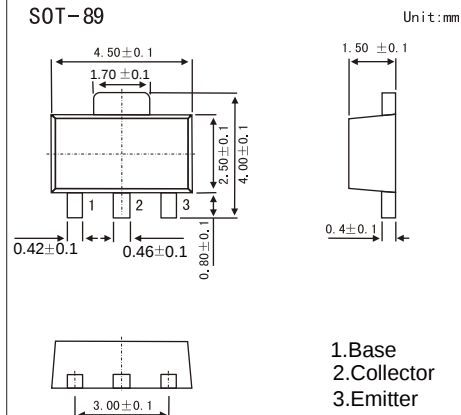
Features

- Excellent hFE linearity and high hFE
hFE = 60 to 400 (VCE = 2 V, IC = 1 A)
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any

SOT-89



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	VCBO	40	V
Collector to Emitter Voltage	VCEO	30	V
Emitter to Base Voltage	VEBO	6	V
Collector Current to Continuous	IC	3	A
Collector Dissipation	PC	0.5	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 to 150	°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	VCBO	IC=100uA ,IE=0	40			V
Collector-emitter breakdown voltage	VCEO	IC= 10 mA , IB=0	30			V
Emitter-base breakdown voltage	VEBO	IE= 100 uA , IC=0	6			V
Collector cut-off current	ICBO	VCB=40 V , IE=0			1	uA
Collector cut-off current	ICEO	VCE=30 V , IB=0			10	uA
Emitter cut-off current	IEBO	VEB=6V , IC=0			1	uA
DC current gain	hFE	VCE= 2V, IC= 1A	60		400	
		VCE=2V, IC= 100mA	32			
Collector-emitter saturation voltage	VCE(sat)	IC=2A, IB= 0.2A			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=2A, IB= 0.2A			1.5	V
Transition frequency	fT	VCE=5 V, IC=0.1mA,f = 10MHz	50			MHz

Classification of hfe(1)

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400
Marking	882R	882Q	882P	882E